

# NGB8245N

## Ignition IGBT 20 A, 450 V, N-Channel D<sup>2</sup>PAK

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Overvoltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

### Features

- Ideal for Coil-on-Plug and Driver-on-Coil Applications
- D<sup>2</sup>PAK Package Offers Smaller Footprint for Increased Board Space
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Low Threshold Voltage for Interfacing Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- This is a Pb-Free Device

### Applications

- Ignition Systems

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

| Rating                                                               | Symbol                            | Value       | Unit                               |
|----------------------------------------------------------------------|-----------------------------------|-------------|------------------------------------|
| Collector-Emitter Voltage                                            | V <sub>CES</sub>                  | 500         | V                                  |
| Collector-Gate Voltage                                               | V <sub>CER</sub>                  | 500         | V                                  |
| Gate-Emitter Voltage                                                 | V <sub>GE</sub>                   | ±15         | V                                  |
| Collector Current-Continuous<br>@ T <sub>C</sub> = 25°C - Pulsed     | I <sub>C</sub>                    | 20<br>50    | A <sub>DC</sub><br>A <sub>AC</sub> |
| Continuous Gate Current                                              | I <sub>G</sub>                    | 1.0         | mA                                 |
| Transient Gate Current<br>(t ≤ 2 ms, f ≤ 100 Hz)                     | I <sub>G</sub>                    | 20          | mA                                 |
| ESD (Charged-Device Model)                                           | ESD                               | 2.0         | kV                                 |
| ESD (Human Body Model)<br>R = 1500 Ω, C = 100 pF                     | ESD                               | 8.0         | kV                                 |
| ESD (Machine Model) R = 0 Ω, C = 200 pF                              | ESD                               | 500         | V                                  |
| Total Power Dissipation @ T <sub>C</sub> = 25°C<br>Derate above 25°C | P <sub>D</sub>                    | 150<br>1.0  | W<br>W/°C                          |
| Operating & Storage Temperature Range                                | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175 | °C                                 |

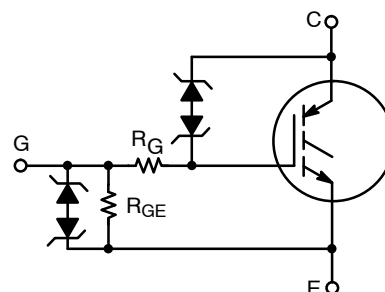
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



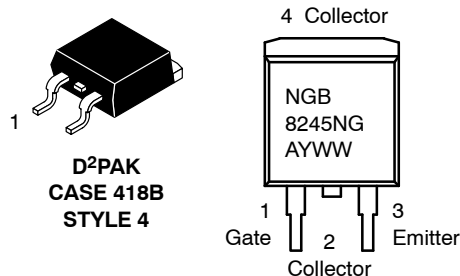
**ON Semiconductor®**

<http://onsemi.com>

**20 A, 450 V**  
**V<sub>CE(on)</sub> ≤ 1.24 V @**  
**I<sub>C</sub> = 15 A, V<sub>GE</sub> ≥ 4.0 V**



### MARKING DIAGRAM



NGB8245N = Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

| Device      | Package                         | Shipping†         |
|-------------|---------------------------------|-------------------|
| NGB8245NT4G | D <sup>2</sup> PAK<br>(Pb-Free) | 800 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS

| Characteristic                                                                                                                                                                                                          | Symbol   | Value | Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|-------|------|
| Single Pulse Collector-to-Emitter Avalanche Energy<br>$V_{CC} = 50\text{ V}$ , $V_{GE} = 5.0\text{ V}$ , $Pk\ I_L = 9.5\text{ A}$ , $R_G = 1\text{ k}\Omega$ , $L = 3.5\text{ mH}$ , Starting $T_C = 150^\circ\text{C}$ | $E_{AS}$ | 158   | mJ   |

## THERMAL CHARACTERISTICS

|                                                                                   |                 |      |                    |
|-----------------------------------------------------------------------------------|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Case                                              | $R_{\theta JC}$ | 1.0  | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction-to-Ambient (Note 1)                                  | $R_{\theta JA}$ | 62.5 | $^\circ\text{C/W}$ |
| Maximum Temperature for Soldering Purposes, 1/8" from case for 5 seconds (Note 2) | $T_L$           | 275  | $^\circ\text{C}$   |

1. When surface mounted to an FR4 board using the minimum recommended pad size.
2. For further details, see Soldering and Mounting Techniques Reference Manual: SOLDERM/D.

## ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Test Conditions | Temperature | Min | Typ | Max | Unit |
|----------------|--------|-----------------|-------------|-----|-----|-----|------|
|----------------|--------|-----------------|-------------|-----|-----|-----|------|

### OFF CHARACTERISTICS (Note 3)

|                                           |               |                                                                                  |                                                 |       |       |     |               |
|-------------------------------------------|---------------|----------------------------------------------------------------------------------|-------------------------------------------------|-------|-------|-----|---------------|
| Collector-Emitter Clamp Voltage           | $BV_{CES}$    | $I_C = 2.0\text{ mA}$                                                            | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 430   | 450   | 470 | V             |
|                                           |               | $I_C = 10\text{ mA}$                                                             | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 450   | 475   | 500 |               |
|                                           |               | $I_C = 12\text{ A}$ , $L = 3.5\text{ mH}$ ,<br>$R_G = 1\text{ k}\Omega$ (Note 4) | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 420   | 450   | 480 |               |
| Collector-Emitter Leakage Current         | $I_{CES}$     | $V_{CE} = 15\text{ V}$ , $V_{GE} = 0\text{ V}$                                   | $T_J = 25^\circ\text{C}$                        |       | 0.002 | 1.0 | $\mu\text{A}$ |
|                                           |               | $V_{CE} = 250\text{ V}$ , $R_G = 1\text{ k}\Omega$                               | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 0.5   | 2.0   | 100 |               |
| Reverse Collector-Emitter Clamp Voltage   | $BV_{CES(R)}$ | $I_C = -75\text{ mA}$                                                            | $T_J = 25^\circ\text{C}$                        | 30    | 33    | 39  | V             |
|                                           |               |                                                                                  | $T_J = 175^\circ\text{C}$                       | 31    | 35    | 40  |               |
|                                           |               |                                                                                  | $T_J = -40^\circ\text{C}$                       | 30    | 31    | 37  |               |
| Reverse Collector-Emitter Leakage Current | $I_{CES(R)}$  | $V_{CE} = -24\text{ V}$                                                          | $T_J = 25^\circ\text{C}$                        | –     | 0.4   | 1.0 | mA            |
|                                           |               |                                                                                  | $T_J = 175^\circ\text{C}$                       | –     | 20    | 35  |               |
|                                           |               |                                                                                  | $T_J = -40^\circ\text{C}$                       | –     | 0.04  | 0.2 |               |
| Gate-Emitter Clamp Voltage                | $BV_{GES}$    | $I_G = \pm 5.0\text{ mA}$                                                        | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 12    | 12.5  | 14  | V             |
| Gate-Emitter Leakage Current              | $I_{GES}$     | $V_{GE} = \pm 5.0\text{ V}$                                                      | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 200   | 316   | 350 | $\mu\text{A}$ |
| Gate Resistor                             | $R_G$         |                                                                                  | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ |       | 70    |     | $\Omega$      |
| Gate-Emitter Resistor                     | $R_{GE}$      |                                                                                  | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 14.25 | 16    | 25  | k $\Omega$    |

### ON CHARACTERISTICS (Note 3)

|                                              |              |                                                |                                                 |     |      |      |                      |
|----------------------------------------------|--------------|------------------------------------------------|-------------------------------------------------|-----|------|------|----------------------|
| Gate Threshold Voltage                       | $V_{GE(th)}$ | $I_C = 1.0\text{ mA}$ , $V_{GE} = V_{CE}$      | $T_J = 25^\circ\text{C}$                        | 1.5 | 1.8  | 2.1  | V                    |
|                                              |              |                                                | $T_J = 175^\circ\text{C}$                       | 0.7 | 1.0  | 1.3  |                      |
|                                              |              |                                                | $T_J = -40^\circ\text{C}$                       | 1.7 | 2.0  | 2.3  |                      |
| Threshold Temperature Coefficient (Negative) |              |                                                |                                                 | 4.0 | 4.6  | 5.2  | mV/ $^\circ\text{C}$ |
| Collector-to-Emitter On-Voltage              | $V_{CE(on)}$ | $I_C = 10\text{ A}$ , $V_{GE} = 3.7\text{ V}$  | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 0.8 | 1.11 | 1.97 | V                    |
|                                              |              | $I_C = 10\text{ A}$ , $V_{GE} = 4.0\text{ V}$  | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 0.8 | 1.10 | 1.85 |                      |
|                                              |              | $I_C = 15\text{ A}$ , $V_{GE} = 4.0\text{ V}$  | $T_J = -40^\circ\text{C to } 175^\circ\text{C}$ | 0.8 | 1.24 | 2.00 |                      |
| Forward Transconductance                     | $g_{fs}$     | $I_C = 6.0\text{ A}$ , $V_{CE} = 5.0\text{ V}$ | $T_J = 25^\circ\text{C}$                        | 10  | 19   | 25   | Mhos                 |

### DYNAMIC CHARACTERISTICS (Note 3)

|                      |           |                                              |                          |      |      |      |    |
|----------------------|-----------|----------------------------------------------|--------------------------|------|------|------|----|
| Input Capacitance    | $C_{ISS}$ | $f = 10\text{ kHz}$ , $V_{CE} = 25\text{ V}$ | $T_J = 25^\circ\text{C}$ | 1100 | 1400 | 1600 | pF |
| Output Capacitance   | $C_{OSS}$ |                                              |                          | 50   | 65   | 80   |    |
| Transfer Capacitance | $C_{RSS}$ |                                              |                          | 15   | 20   | 25   |    |

# NGB8245N

## ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Test Conditions | Temperature | Min | Typ | Max | Unit |
|----------------|--------|-----------------|-------------|-----|-----|-----|------|
|----------------|--------|-----------------|-------------|-----|-----|-----|------|

### SWITCHING CHARACTERISTICS (Note 3)

|                                                              |               |                                                                                                                             |                                                  |     |     |      |               |
|--------------------------------------------------------------|---------------|-----------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------|-----|-----|------|---------------|
| Turn-On Delay Time (Resistive)<br>10% $V_{GE}$ to 10% $I_C$  | $t_{d(on)R}$  | $V_{CC} = 14\text{ V}$ , $R_L = 1.0\ \Omega$ ,<br>$R_G = 1.0\text{ k}\Omega$ , $V_{GE} = 5.0\text{ V}$                      | $T_J = -40^\circ\text{C}$ to $175^\circ\text{C}$ | 0.1 | 1.0 | 2.0  | $\mu\text{s}$ |
| Rise Time (Resistive)<br>10% $I_C$ to 90% $I_C$              | $t_{rR}$      |                                                                                                                             | $T_J = -40^\circ\text{C}$ to $175^\circ\text{C}$ | 1.0 | 3.4 | 6.0  |               |
| Turn-Off Delay Time (Resistive)<br>90% $V_{GE}$ to 90% $I_C$ | $t_{d(off)R}$ | $V_{CC} = 14\text{ V}$ , $R_L = 1.0\ \Omega$ ,<br>$R_G = 1.0\text{ k}\Omega$ , $V_{GE} = 5.0\text{ V}$                      | $T_J = -40^\circ\text{C}$ to $175^\circ\text{C}$ | 2.0 | 4.5 | 8.0  | $\mu\text{s}$ |
| Fall Time (Resistive)<br>90% $I_C$ to 10% $I_C$              | $t_{fR}$      |                                                                                                                             | $T_J = -40^\circ\text{C}$ to $175^\circ\text{C}$ | 3.0 | 8.0 | 12   |               |
| Turn-Off Delay Time (Inductive)<br>90% $V_{GE}$ to 90% $I_C$ | $t_{d(off)L}$ | $V_{CE} = BV_{CES}$ , $L = 0.5\text{mH}$ ,<br>$R_G = 1.0\text{ k}\Omega$ , $I_C = 10\text{ A}$ ,<br>$V_{GE} = 5.0\text{ V}$ | $T_J = -40^\circ\text{C}$ to $175^\circ\text{C}$ | 6.5 | 9.7 | 12.5 | $\mu\text{s}$ |
| Fall Time (Inductive)<br>90% $I_C$ to 10% $I_C$              | $t_{fL}$      |                                                                                                                             | $T_J = -40^\circ\text{C}$ to $175^\circ\text{C}$ | 6.0 | 8.3 | 11   |               |

3. Electrical Characteristics at temperature other than  $25^\circ\text{C}$ , Dynamic and Switching characteristics are not subject to production testing.

4. Not subject to production testing.

TYPICAL ELECTRICAL CHARACTERISTICS

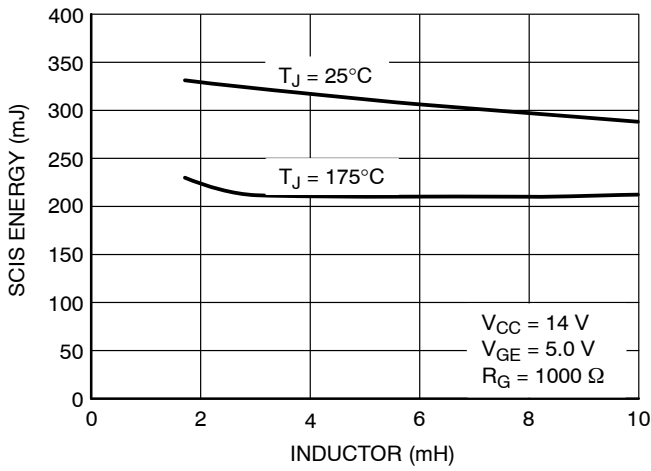


Figure 1. Self Clamped Inductive Switching

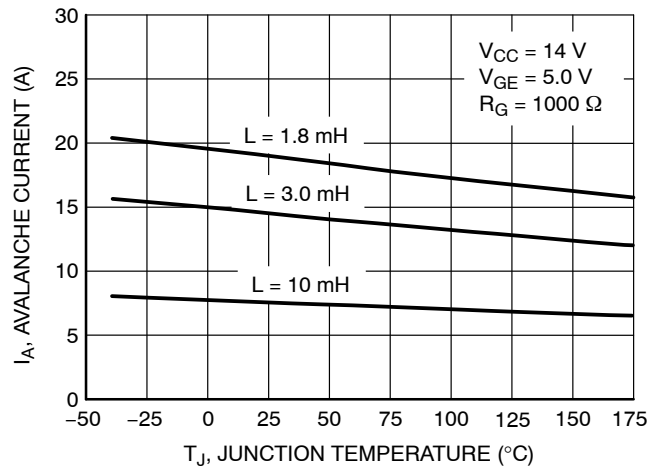


Figure 2. Open Secondary Avalanche Current vs. Temperature

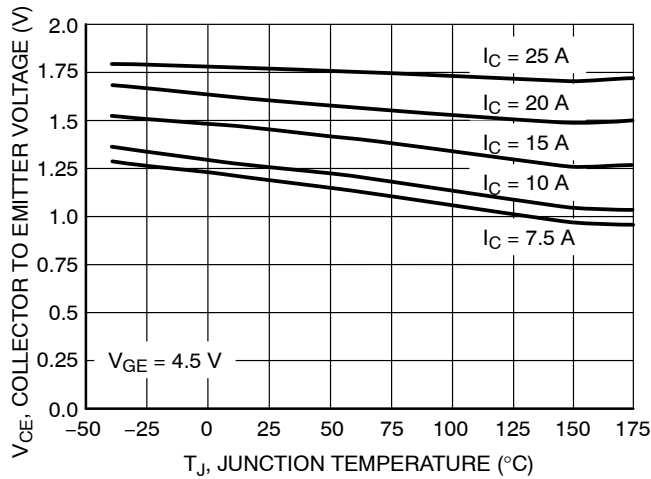


Figure 3. Collector-to-Emitter Voltage vs. Junction Temperature

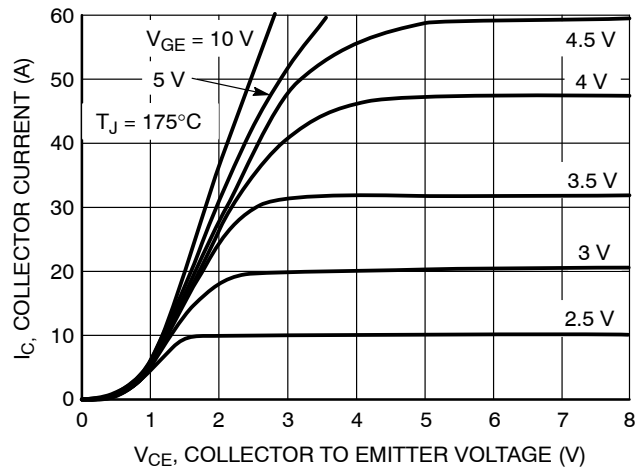


Figure 4. Collector Current vs. Collector-to-Emitter Voltage

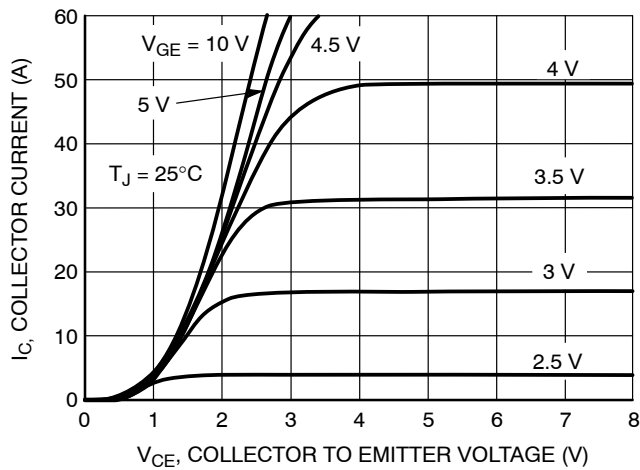


Figure 5. Collector Current vs. Collector-to-Emitter Voltage

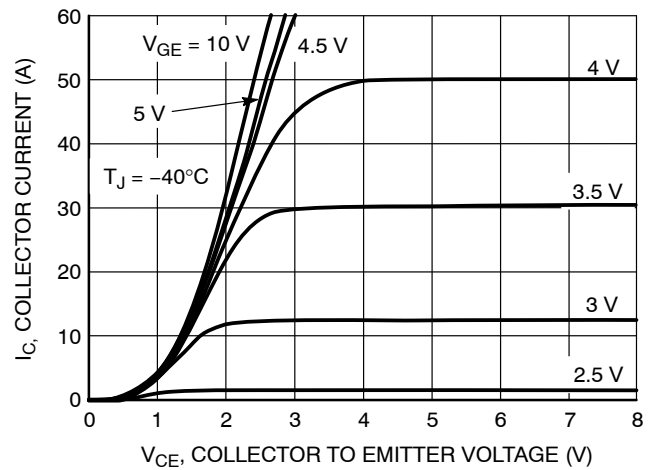


Figure 6. Collector Current vs. Collector-to-Emitter Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

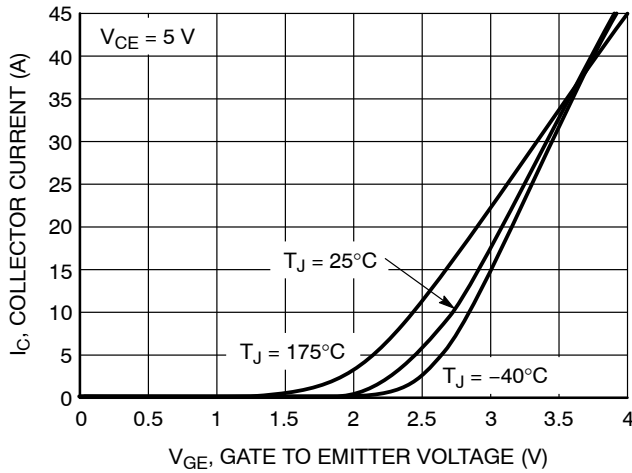


Figure 7. Transfer Characteristics

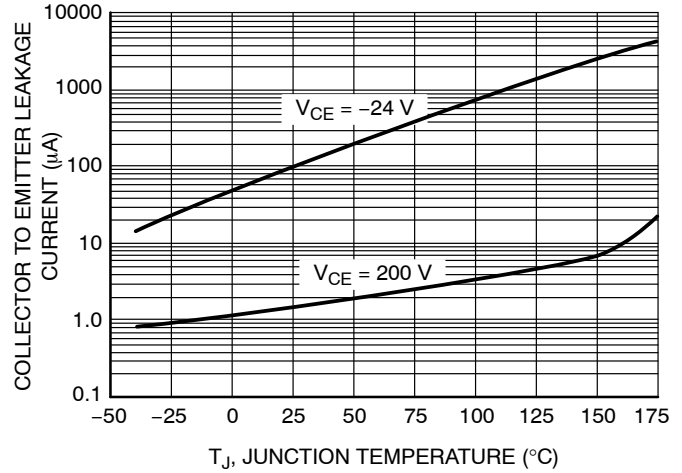


Figure 8. Collector-to-Emitter Leakage Current vs. Temperature

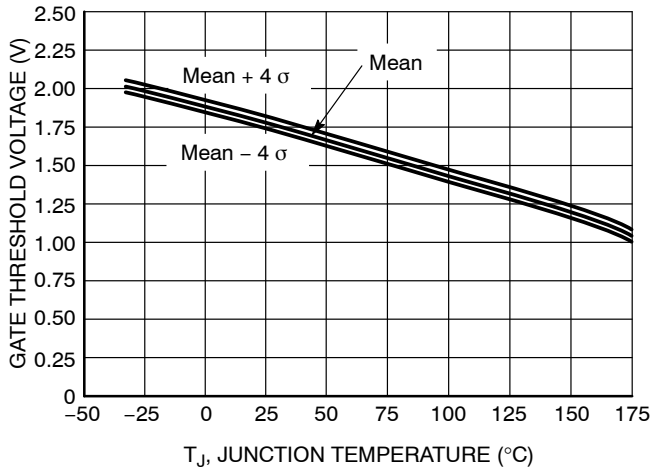


Figure 9. Gate Threshold Voltage vs. Temperature

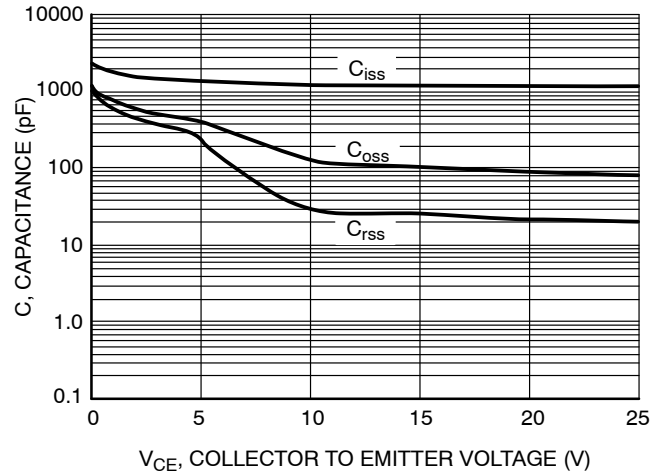


Figure 10. Capacitance vs. Collector-to-Emitter Voltage

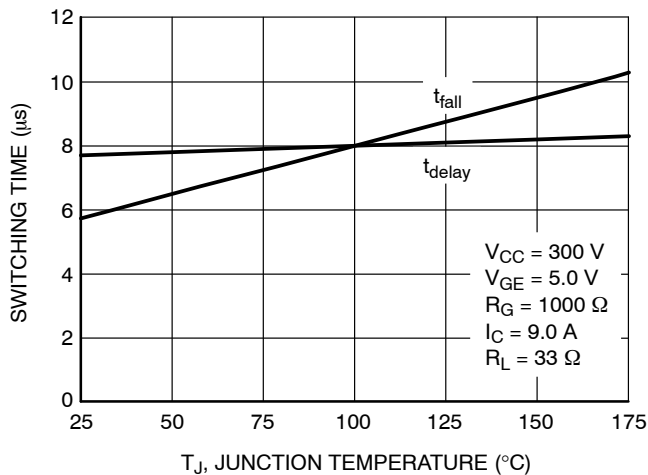


Figure 11. Resistive Switching Fall Time vs. Temperature

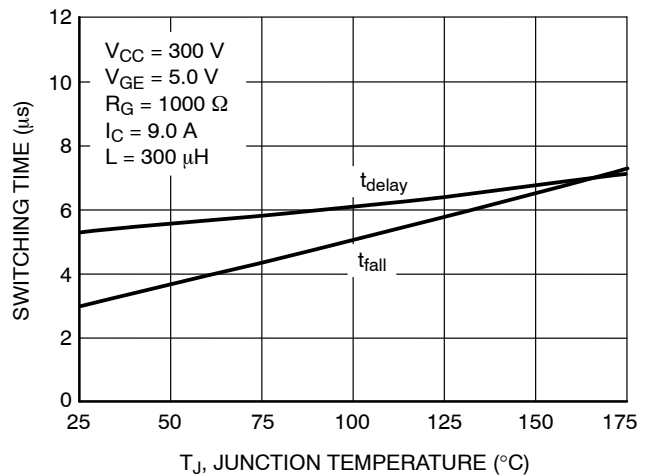
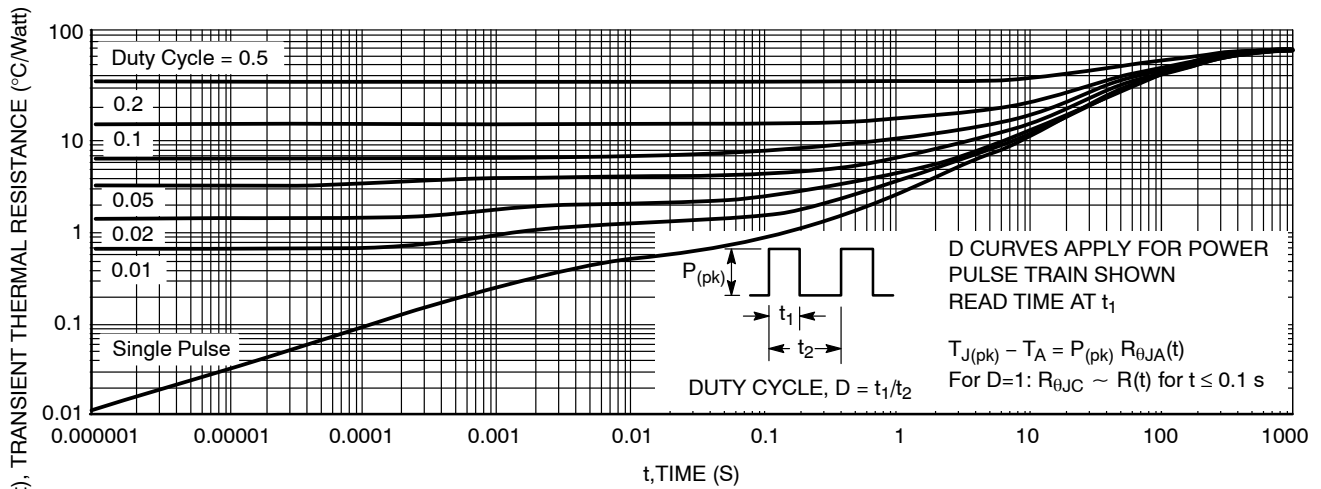
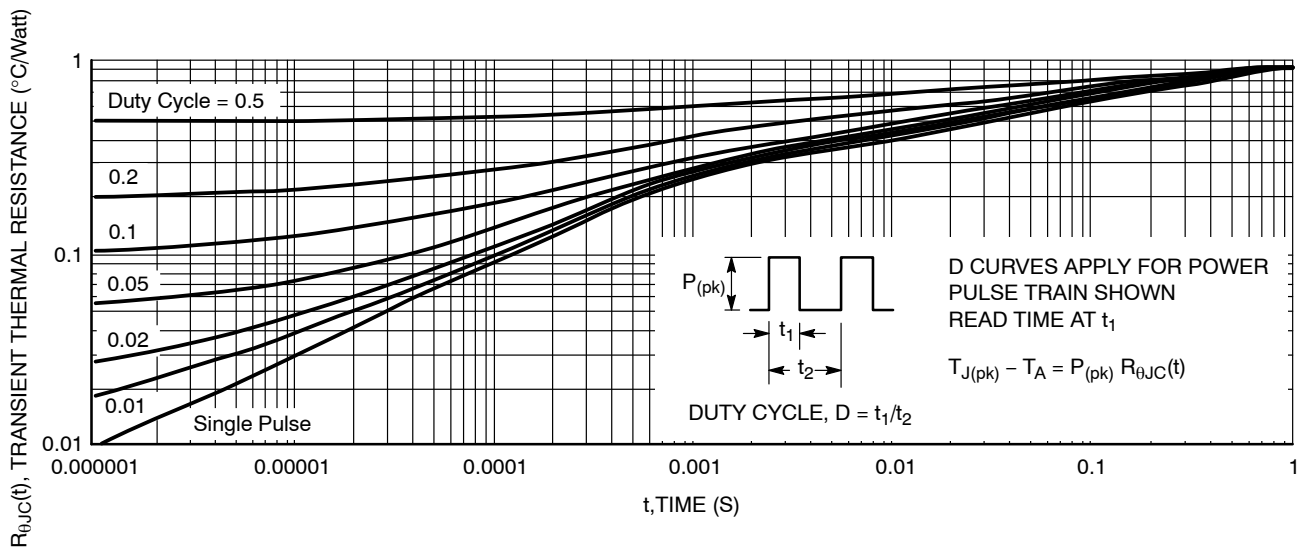


Figure 12. Inductive Switching Fall Time vs. Temperature



**Figure 13. Minimum Pad Transient Thermal Resistance  
(Non-normalized Junction-to-Ambient)**

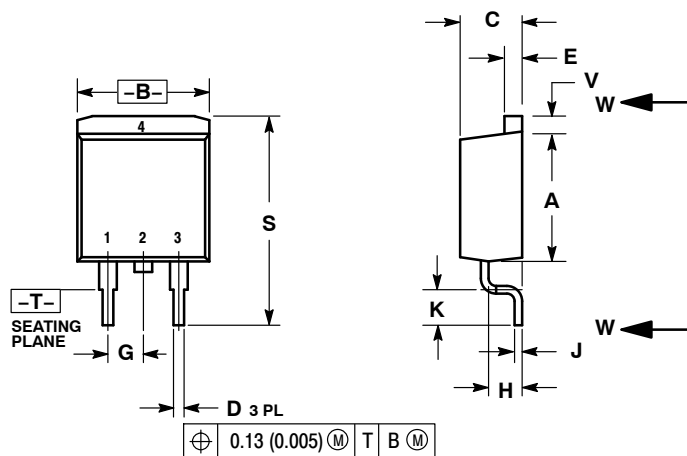


**Figure 14. Best Case Transient Thermal Resistance  
(Non-normalized Junction-to-Case Mounted on Cold Plate)**

# NGB8245N

## PACKAGE DIMENSIONS

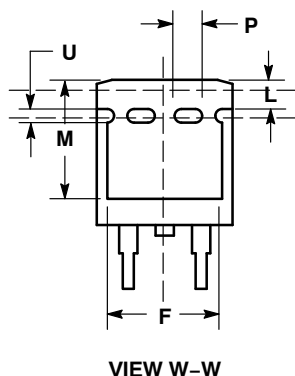
### D<sup>2</sup>PAK 3 CASE 418B-04 ISSUE K



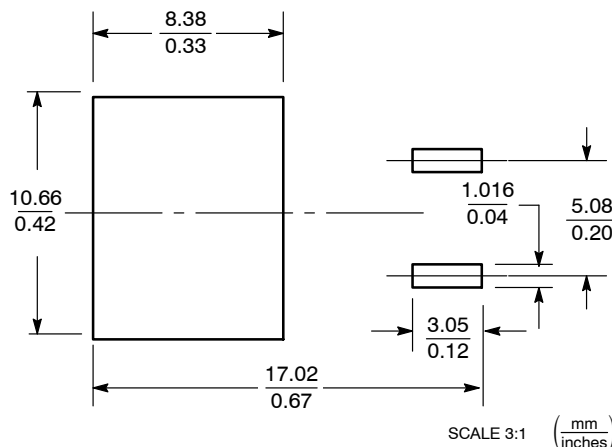
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| DIM | INCHES    |       | MILLIMETERS |       |
|-----|-----------|-------|-------------|-------|
|     | MIN       | MAX   | MIN         | MAX   |
| A   | 0.340     | 0.380 | 8.64        | 9.65  |
| B   | 0.380     | 0.405 | 9.65        | 10.29 |
| C   | 0.160     | 0.190 | 4.06        | 4.83  |
| D   | 0.020     | 0.035 | 0.51        | 0.89  |
| E   | 0.045     | 0.055 | 1.14        | 1.40  |
| F   | 0.310     | 0.350 | 7.87        | 8.89  |
| G   | 0.100 BSC |       | 2.54 BSC    |       |
| H   | 0.080     | 0.110 | 2.03        | 2.79  |
| J   | 0.018     | 0.025 | 0.46        | 0.64  |
| K   | 0.090     | 0.110 | 2.29        | 2.79  |
| L   | 0.052     | 0.072 | 1.32        | 1.83  |
| M   | 0.280     | 0.320 | 7.11        | 8.13  |
| N   | 0.197 REF |       | 5.00 REF    |       |
| P   | 0.079 REF |       | 2.00 REF    |       |
| R   | 0.039 REF |       | 0.99 REF    |       |
| S   | 0.575     | 0.625 | 14.60       | 15.88 |
| V   | 0.045     | 0.055 | 1.14        | 1.40  |

- STYLE 4:
- PIN 1. GATE
  - COLLECTOR
  - EMITTER
  - COLLECTOR



### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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